

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY							
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a	Q _g (Typ.)				
30	0.030 at V _{GS} = 10 V	6.5	4.5 nC				
30	0.033 at V _{GS} = 4.5 V	6.0	4.5110				

FEATURES

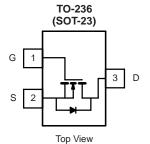
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

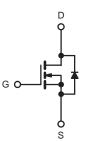


ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

DC/DC Converter





N-Channel MOSFET

ABSOLUTE MAXIMUM RATIN	GS $T_A = 25 ^{\circ}C$,	unless othe	erwise noted	
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	_ v
	T _C = 25 °C		6.5 ^a	
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 70 °C	I _D	6.0	
Continuous Diain Current (1) = 130 C)	T _A = 25 °C		5.3	
	T _A = 70 °C		5.0	Α
Pulsed Drain Current		I _{DM}	25	
	T _C = 25 °C		1.4	7
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	0.9 ^{b, c}	
	T _C = 25 °C		1.7	
Maximum Power Dissipation	$T_C = 70 ^{\circ}C$	P _D	1.1	w
	$T_A = 25 ^{\circ}C$		1.1 ^{b, c}	
	T _A = 70 °C		0.7 ^{b, c}	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}			260	

THERMAL RESISTANCE RATINGS								
Parameter		Symbol	Typical	Maximum	Unit			
Maximum Junction-to-Ambient ^{b, d}	t ≤ 5 s	R_{thJA}	90	115	°C/W			
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	60	75	7 0,00			

Notes:

- a. Package limited
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. Maximum under steady state conditions is 130 °C/W.



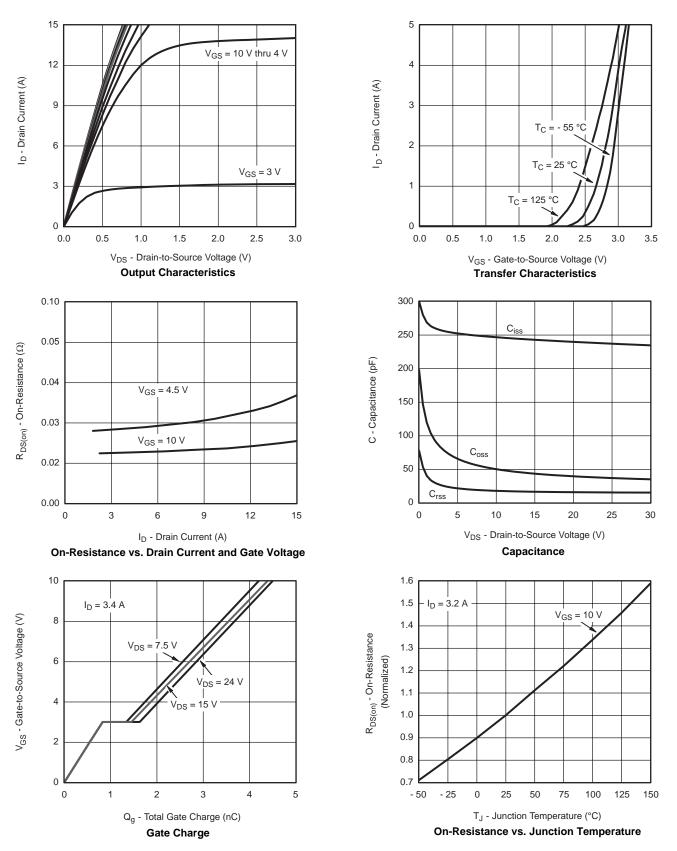
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						•
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$				V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		31		\//00
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_{J}$	I _D = 250 μA		- 5		mv/°C
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.7	1.1	2.0	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zana Oata Waltana Busin Oamani	1 . 1	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10	μΑ
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			Α
	_	$V_{GS} = 10 \text{ V}, I_D = 3.2 \text{ A}$		0.030		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 2.8 \text{ A}$		0.033		Ω
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 4.8 \text{ A}$		11		S
Dynamic ^b	l				L	
Input Capacitance	C _{iss}			335		
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		45		V mV/°C V nA μA A Ω S S PF nC Ω Ω NS nC
Reverse Transfer Capacitance	C _{rss}			17		
Tatal Oata Ohaana	Qg	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 3.4 \text{ A}$		4.5	6.7	nC
Total Gate Charge				2.1	3.2	
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 3.4 \text{ A}$		0.85		
Gate-Drain Charge	Q_{gd}			0.65		
Gate Resistance	R_{g}	f = 1 MHz	0.8	4.4	8.8	Ω
Turn-On Delay Time	t _{d(on)}			12	20	
Rise Time	t _r	V_{DD} = 15 V, R_L = 5.6 Ω		50	75	- ns
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 2.7 A, V_{GEN} = 4.5 V, R_g = 1 Ω		12	20	
Fall Time	t _f			22	35	
Turn-On Delay Time	t _{d(on)}			5	10	
Rise Time	t _r	V_{DD} = 15 V, R_L = 5.6 Ω		12	20	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 2.7 A, V_{GEN} = 10 V, R_g = 1 Ω		10	15	
Fall Time	t _f			5	10	
Drain-Source Body Diode Characteristi	cs				L	1
Continuous Source-Drain Diode Current	I _S	$T_C = 25 ^{\circ}C$			1.4	۸
Pulse Diode Forward Current	I _{SM}				15	
Body Diode Voltage	V_{SD}	$I_S = 2.7 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}			10	20	ns
Body Diode Reverse Recovery Charge	Q _{rr}	L = 2.7 A dl/dt = 100 A/vo T = 25.00		5	10	nC
Reverse Recovery Fall Time	t _a	$I_F = 2.7 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		6		
Reverse Recovery Rise Time	t _b			4		ns

Notes:

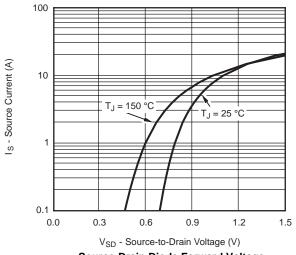
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

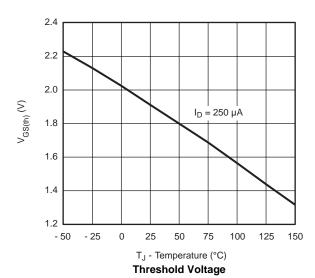








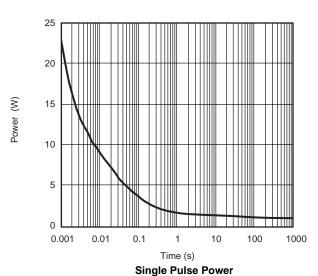
Source-Drain Diode Forward Voltage



100

 $C_{J} = 0.14$ $C_{J} = 0.12$ $C_{J} = 0.10$ $C_{J} = 0.08$ C_{J

On-Resistance vs. Gate-to-Source Voltage



Limited by R_{DS(on)*}

10

10 μs

1 ms

1 ms

100 ms

100 ms

1 s, 10 s

DC

T_A = 25 °C

Single Pulse

BVDSS Limited

0.01

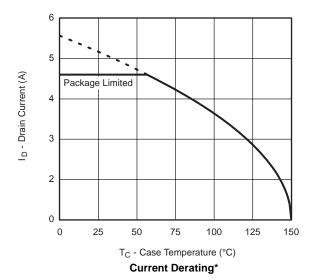
0.1

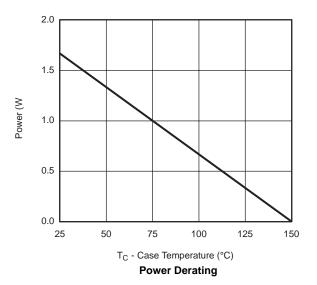
1 10 100

 $V_{DS} \text{ - Drain-to-Source Voltage (V)} \\ \text{* V}_{GS} \text{ > minimum V}_{GS} \text{ at which R}_{DS(on)} \text{ is specified}$

Safe Operating Area, Junction-to-Ambient

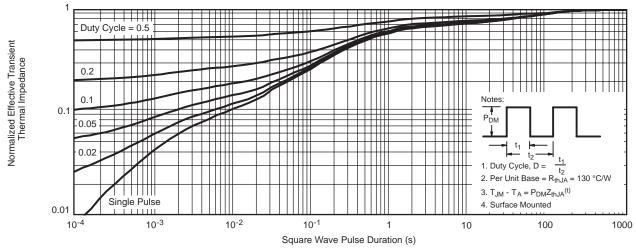






^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





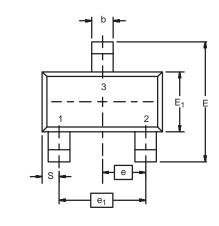
Normalized Thermal Transient Impedance, Junction-to-Ambient

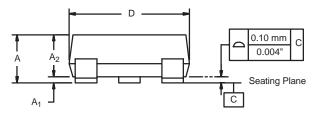


Normalized Thermal Transient Impedance, Junction-to-Foot



SOT-23 (TO-236): 3-LEAD





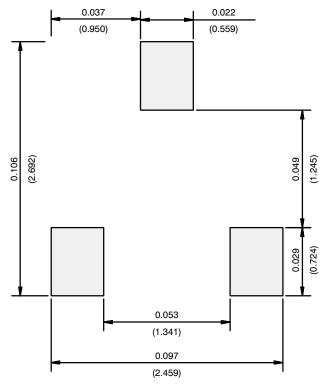


Dim	MILLIM	ETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90	1.90 BSC		8 Ref	
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025	5 Ref	
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	

DWG: 5479



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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